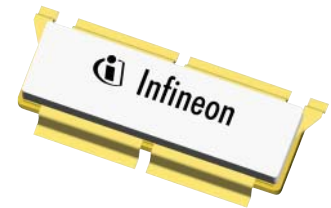


Thermally-Enhanced High Power RF LDMOS FET 320 W, 28 V, 2110 – 2170 MHz

Description

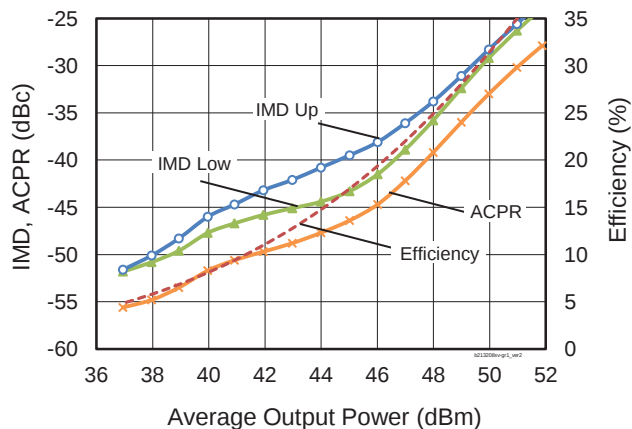
The PTFB213208SV is a 320-watt LDMOS FET intended for use in multi-standard cellular power amplifier applications in the 2110 to 2170 MHz frequency band. Features include input and output matching, high gain and thermally-enhanced package with earless flange. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.

PTFB213208SV
Package H-37275G-6/2
(formed leads)



Two-carrier WCDMA 3GPP Drive-up

$V_{DD} = 28\text{ V}$, $I_{DQ} = 2.65\text{ A}$, $f = 2170\text{ MHz}$,
3GPP WCDMA signal, PAR = 8 dB,
10 MHz carrier spacing, BW = 3.84 MHz



Features

- Broadband internal matching
- Wide video bandwidth
- Typical pulsed CW performance, 2140 MHz, 28 V (combined outputs)
 - Output power @ P_{1dB} = 343 W
 - Efficiency = 54%
 - Gain = 16.5 dB
- Typical single-carrier WCDMA performance, 2140 MHz, 28 V
 - Output power = 50 dBm avg
 - Gain = 17 dB
 - Efficiency = 32%
- Capable of handling 10:1 VSWR @ 28 V, 320 W (CW) output power
- Integrated ESD protection
- Low thermal resistance
- Pb-free and RoHS compliant

RF Characteristics

Single-carrier WCDMA Specifications (device with straight leads, tested in Infineon test fixture)

$V_{DD} = 28\text{ V}$, $I_{DQ} = 2.6\text{ A}$, $P_{OUT} = 85\text{ W}$ average, $f = 2170\text{ MHz}$
3GPP WCDMA signal, 3.84 MHz channel bandwidth, peak/average = 10 dB @ 0.01% CCDF

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	Gps	15.75	17	—	dB
Drain Efficiency	η_D	29	32	—	%
Adjacent Channel Power Ratio	ACPR	—	-35	-29.5	dBc

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

DC Characteristics (both sides)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	65	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1.0	μA
	$V_{DS} = 63\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	10.0	μA
On-State Resistance	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.05	—	Ω
Operating Gate Voltage	$V_{DS} = 28\text{ V}$, $I_{DQ} = 2.6\text{ A}$	V_{GS}	2.3	2.8	3.3	V
Gate Leakage Current	$V_{GS} = 10\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	—	—	1.0	μA

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	65	V
Gate-Source Voltage	V_{GS}	−6 to +10	V
Junction Temperature	T_J	225	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	−40 to +150	$^{\circ}\text{C}$
Thermal Resistance ($T_{CASE} = 70^{\circ}\text{C}$, 200 W CW)	$R_{\theta JC}$	0.20	$^{\circ}\text{C/W}$

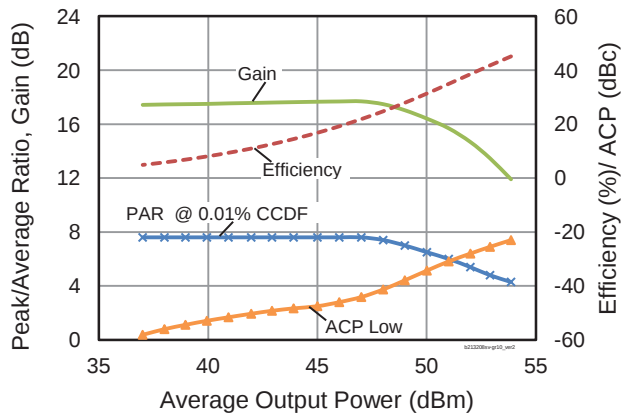
Ordering Information

Type and Version	Order Code	Package Description	Shipping
PTFB213208SV V2 R250	PTFB213208SVV2R250XTMA1	H-37275G-6/2, earless flange	Tape & Reel, 250 pcs

Typical Performance (data taken in a production test fixture)

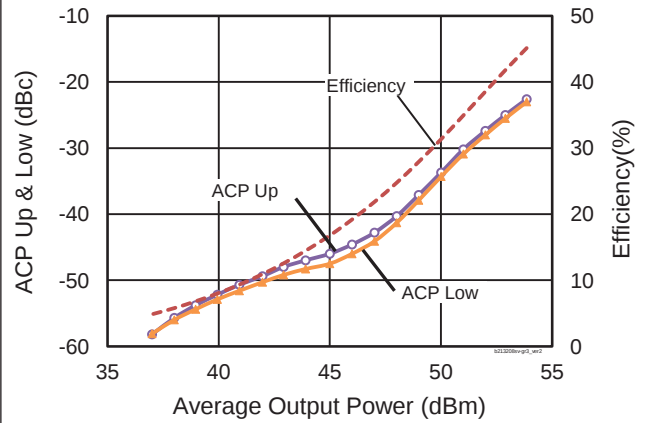
Single-carrier WCDMA 3GPP Drive-up

$V_{DD} = 28\text{ V}$, $I_{DQ} = 2.7\text{ A}$, $f = 2170\text{ MHz}$
 3GPP WCDMA signal,
 PAR = 7.5 dB, 3.84 MHz BW



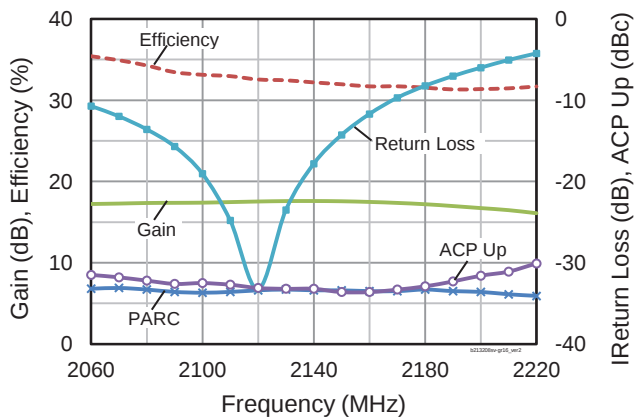
Single-carrier WCDMA 3GPP Drive-up

$V_{DD} = 28\text{ V}$, $I_{DQ} = 2.7\text{ A}$, $f = 2170\text{ MHz}$,
 3GPP WCDMA signal, PAR = 7.5 dB,
 BW = 3.84 MHz



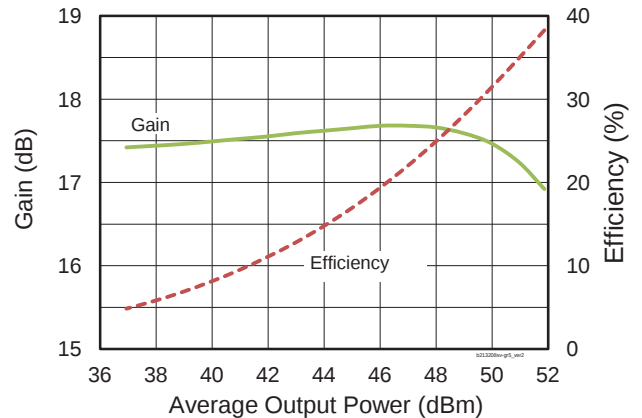
Single-carrier WCDMA 3GPP Broadband

$V_{DD} = 28\text{ V}$, $I_{DQ} = 2.7\text{ A}$, $P_{OUT} = 100\text{ W}$



Two-carrier WCDMA 3GPP Drive-up

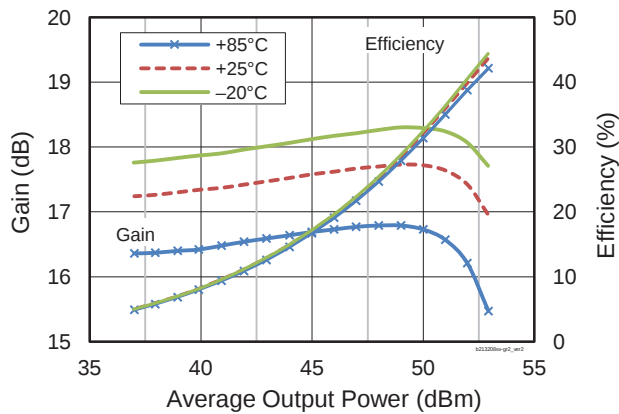
$V_{DD} = 28\text{ V}$, $I_{DQ} = 2.65\text{ A}$, $f = 2170\text{ MHz}$,
 3GPP WCDMA signal, PAR = 8 dB,
 10 MHz carrier spacing, BW = 3.84 MHz



Typical Performance (cont.)

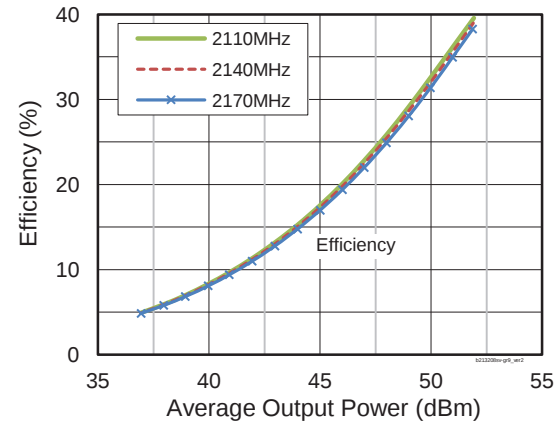
Two-tone Drive-up (over temperature)

$V_{DD} = 28\text{ V}$, $I_{DQ} = 2.7\text{ A}$,
 $f_1 = 2139.5\text{ MHz}$, $f_2 = 2140.5\text{ MHz}$



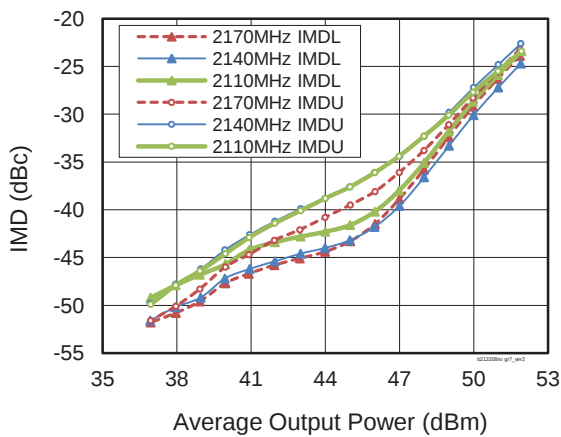
Two-carrier WCDMA 3GPP Drive-up

$V_{DD} = 28\text{ V}$, $I_{DQ} = 2.7\text{ A}$,
 $f = 2110, 2140, 2170\text{ MHz}$,
 3GPP WCDMA signal, PAR = 8 dB,
 10 MHz carrier spacing, BW = 3.84 MHz



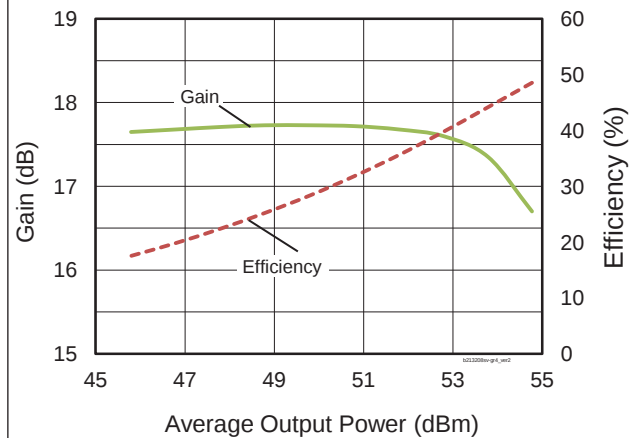
Two-carrier WCDMA 3GPP Drive-up

$V_{DD} = 30\text{ V}$, $I_{DQ} = 2.65\text{ A}$,
 3GPP WCDMA, PAR = 8 dB,
 10 MHz carrier spacing, BW = 3.84 MHz



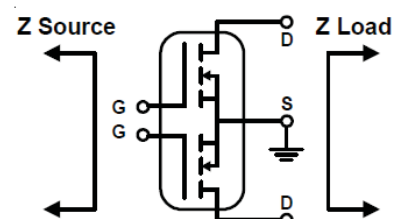
CW Drive-up

$V_{DD} = 28\text{ V}$, $I_{DQ} = 2.7\text{ A}$, $f = 2170\text{ MHz}$



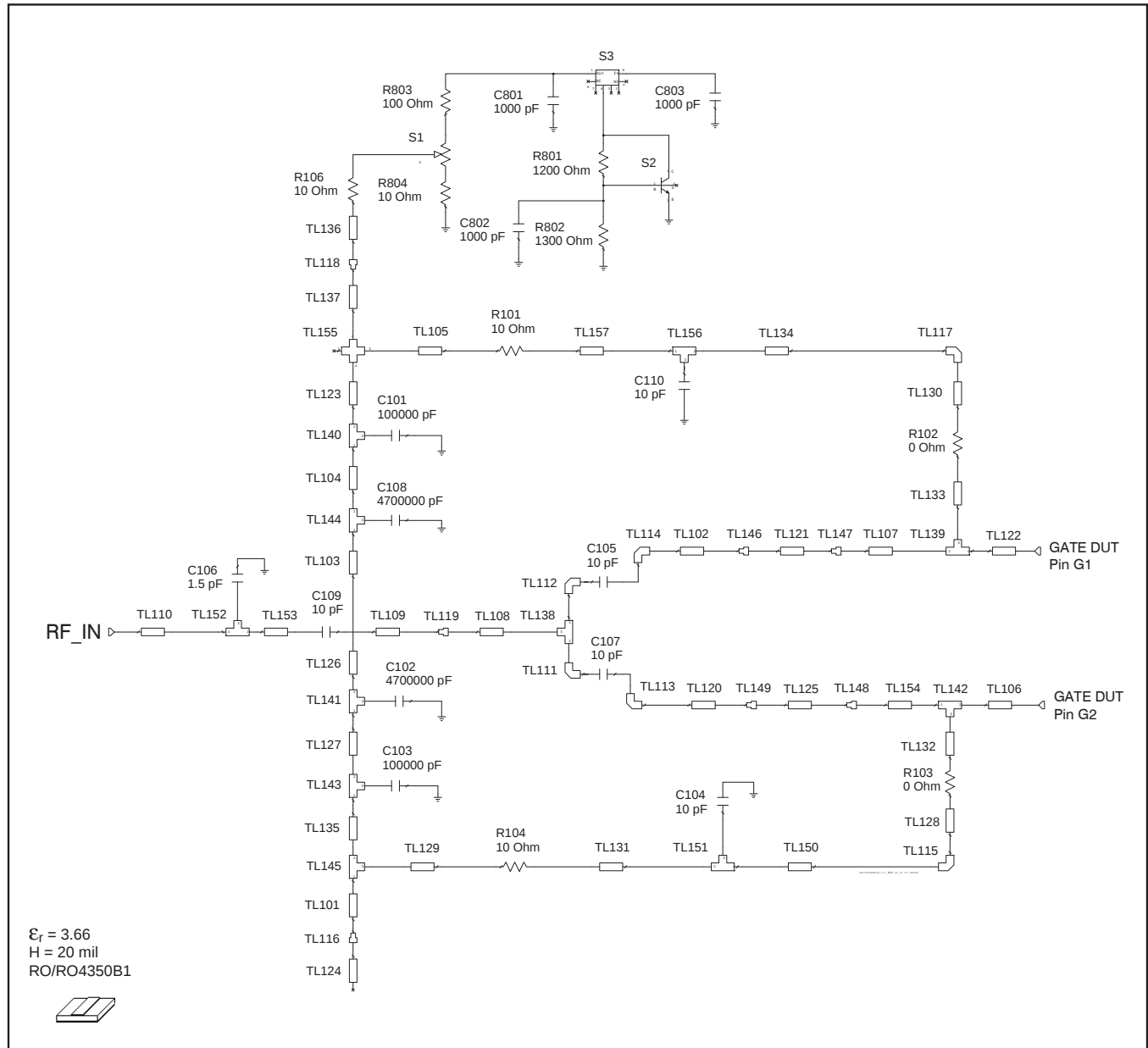
Broadband Circuit Impedance

Frequency MHz	Z Source Ω		Z Load Ω	
	R	jX	R	jX
2080	2.84	-5.14	0.97	-2.70
2090	2.82	-5.14	0.95	-2.69
2100	2.79	-5.15	0.93	-2.67
2110	2.77	-5.15	0.92	-2.65
2120	2.74	-5.16	0.90	-2.64
2130	2.71	-5.16	0.88	-2.62
2140	2.67	-5.17	0.86	-2.60
2150	2.64	-5.18	0.85	-2.58
2160	2.60	-5.18	0.83	-2.56
2170	2.57	-5.19	0.81	-2.54
2180	2.53	-5.19	0.79	-2.53
2190	2.48	-5.19	0.78	-2.51
2200	2.44	-5.19	0.76	-2.48



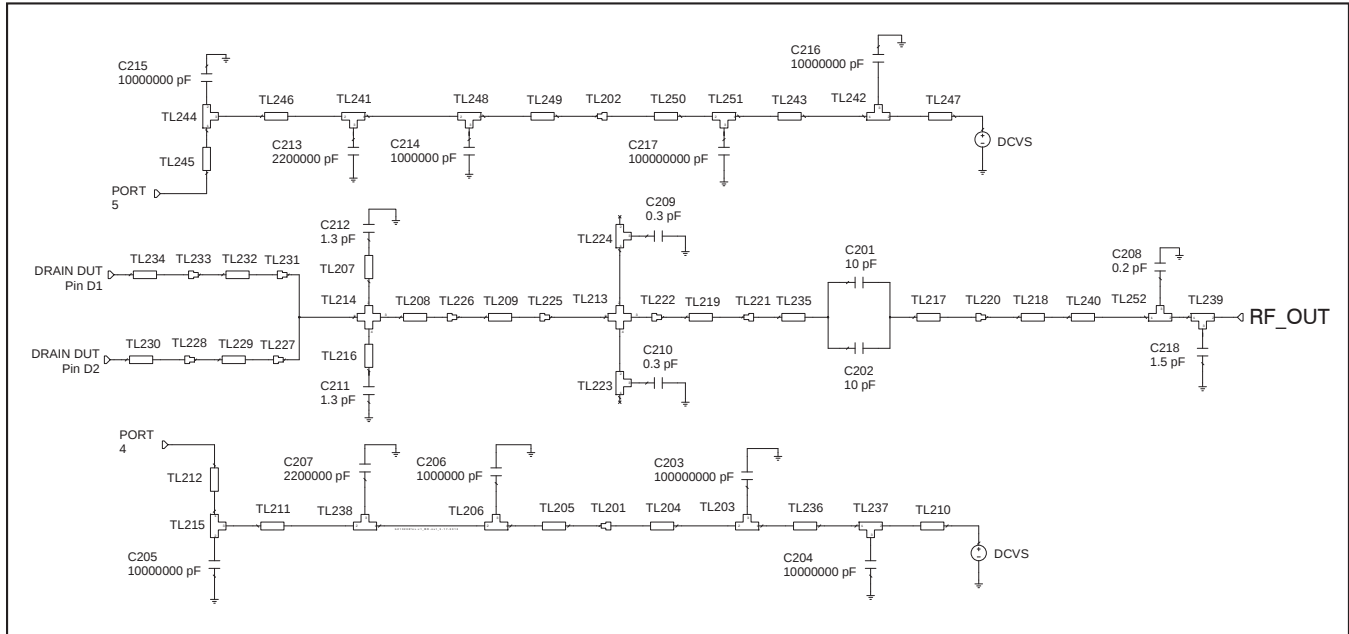
See next page for reference circuit information

Reference Circuit



Reference circuit input schematic for $f = 2170$ MHz

Reference Circuit (cont.)



Reference circuit output schematic for $f = 2170$ MHz

Reference Circuit Assembly

DUT PTFB213208SV

Reference Circuit Part No. LTN/PTFB213208SV

PCB Rogers RO4350, 0.508 mm [0.020"] thick, 2 oz. copper, $\epsilon_r = 3.66$

Find Gerber files for this reference fixture on the Infineon Web site at <http://www.infineon.com/rfpower>

Electrical Characteristics at 2170 MHz

Transmission Line	Electrical Characteristics	Dimensions: mm	Dimensions: mils
Input			
TL101	0.006λ , 62.65Ω	$W = 0.76$, $L = 0.51$	$W = 30$, $L = 30$
TL102	0.010λ , 28.26Ω	$W = 2.54$, $L = 0.76$	$W = 100$, $L = 100$
TL103	0.171λ , 62.65Ω	$W = 0.76$, $L = 14.2$	$W = 30$, $L = 30$
TL104	0.010λ , 62.65Ω	$W = 0.76$, $L = 0.81$	$W = 30$, $L = 30$
TL105	0.020λ , 53.11Ω	$W = 1.02$, $L = 1.65$	$W = 40$, $L = 40$
TL106	0.072λ , 7.13Ω	$W = 12.7$, $L = 5.36$	$W = 500$, $L = 500$
TL107	0.017λ , 7.13Ω	$W = 12.7$, $L = 1.3$	$W = 500$, $L = 500$
TL108	0.026λ , 31.94Ω	$W = 2.16$, $L = 2.03$	$W = 85$, $L = 85$
TL109	0.061λ , 48.71Ω	$W = 1.17$, $L = 5.02$	$W = 46$, $L = 46$
TL110	0.006λ , 48.71Ω	$W = 1.17$, $L = 0.51$	$W = 46$, $L = 46$
TL120	0.010λ , 28.26Ω	$W = 2.54$, $L = 0.76$	$W = 100$, $L = 100$
TL121	0.023λ , 16.69Ω	$W = 4.88$, $L = 1.78$	$W = 192$, $L = 192$
TL122	0.072λ , 7.13Ω	$W = 12.7$, $L = 5.36$	$W = 500$, $L = 500$

(table cont. next page)

Reference Circuit (cont.)

Electrical Characteristics at 2170 MHz (Input cont.)

Transmission Line	Electrical Characteristics	Dimensions: mm	Dimensions: mils
TL123	0.043λ , 62.65Ω	$W = 0.76$, $L = 3.56$	$W = 30$, $L = 30$
TL124, TL136	0.016λ , 33.39Ω	$W = 2.03$, $L = 1.27$	$W = 80$, $L = 80$
TL125	0.023λ , 16.69Ω	$W = 4.88$, $L = 1.78$	$W = 192$, $L = 192$
TL126	0.031λ , 62.65Ω	$W = 0.76$, $L = 2.54$	$W = 30$, $L = 30$
TL127	0.011λ , 62.65Ω	$W = 0.76$, $L = 0.89$	$W = 30$, $L = 30$
TL128, TL130	0.006λ , 53.11Ω	$W = 1.02$, $L = 0.51$	$W = 40$, $L = 40$
TL129	0.019λ , 53.11Ω	$W = 1.02$, $L = 1.53$	$W = 40$, $L = 40$
TL131, TL157	0.017λ , 53.11Ω	$W = 1.02$, $L = 1.42$	$W = 40$, $L = 40$
TL132, TL133	0.009λ , 53.11Ω	$W = 1.02$, $L = 0.76$	$W = 40$, $L = 40$
TL134	0.100λ , 53.11Ω	$W = 1.02$, $L = 8.2$	$W = 40$, $L = 40$
TL135	0.045λ , 62.65Ω	$W = 0.76$, $L = 3.71$	$W = 30$, $L = 30$
TL137	0.003λ , 62.65Ω	$W = 0.76$, $L = 0.28$	$W = 30$, $L = 30$
TL138	0.027λ , 28.26Ω	$W1 = 2.54$, $W2 = 2.54$, $W3 = 2.16$	$W1 = 100$, $W2 = 100$, $W3 = 85$
TL139, TL142	0.014λ , 7.13Ω	$W1 = 12.7$, $W2 = 12.7$, $W3 = 1.02$	$W1 = 500$, $W2 = 500$, $W3 = 40$
TL140, TL141, TL143, TL144	0.015λ , 62.65Ω	$W1 = 0.76$, $W2 = 0.76$, $W3 = 1.27$	$W1 = 30$, $W2 = 30$, $W3 = 50$
TL145	0.012λ , 62.65Ω	$W1 = 0.76$, $W2 = 0.76$, $W3 = 1.02$	$W1 = 30$, $W2 = 30$, $W3 = 40$
TL150	0.102λ , 53.11Ω	$W = 1.02$, $L = 8.36$	$W = 40$, $L = 40$
TL151, TL156	0.015λ , 53.11Ω	$W1 = 1.02$, $W2 = 1.02$, $W3 = 1.27$	$W1 = 40$, $W2 = 40$, $W3 = 50$
TL152	0.016λ , 48.71Ω	$W1 = 1.17$, $W2 = 1.17$, $W3 = 1.27$	$W1 = 46$, $W2 = 46$, $W3 = 50$
TL153	0.012λ , 48.71Ω	$W = 1.17$, $L = 0.97$	$W = 46$, $L = 46$
TL154	0.017λ , 7.13Ω	$W = 12.7$, $L = 1.3$	$W = 500$, $L = 500$
TL155	0.009λ , 46.18Ω	$W1 = 1.27$, $W2 = 0.76$, $W3 = 1.27$, $W4$	$W1 = 50$, $W2 = 50$, $W3 = 50$, $W4 = 30$

Output

TL203	0.027λ , 11.33Ω	$W1 = 7.62$, $W2 = 7.62$, $W3 = 2.03$	$W1 = 300$, $W2 = 300$, $W3 = 80$
TL204	0.029λ , 11.33Ω	$W = 7.62$, $L = 2.18$	$W = 300$, $L = 300$
TL205	0.091λ , 20.5Ω	$W = 3.81$, $L = 7.11$	$W = 150$, $L = 150$
TL206	0.029λ , 20.5Ω	$W1 = 3.81$, $W2 = 3.81$, $W3 = 2.29$	$W1 = 150$, $W2 = 150$, $W3 = 90$
TL207, TL216	0.000λ , 141.78Ω	$W = 0.03$, $L = 0.03$	$W = 1$, $L = 1$
TL208	0.009λ , 4.2Ω	$W = 22.35$, $L = 0.65$	$W = 880$, $L = 880$
TL209	0.021λ , 7.75Ω	$W = 11.61$, $L = 1.6$	$W = 457$, $L = 457$
TL210	0.013λ , 11.33Ω	$W = 7.62$, $L = 1.02$	$W = 300$, $L = 300$
TL211	0.017λ , 20.5Ω	$W = 3.81$, $L = 1.3$	$W = 150$, $L = 150$
TL212	0.100λ , 20.5Ω	$W = 3.81$, $L = 7.8$	$W = 150$, $L = 150$
TL213	0.003λ , 10.21Ω	$W1 = 8.56$, $W2 = 0.25$, $W3 = 8.56$, $W4$	$W1 = 337$, $W2 = 337$, $W3 = 337$, $W4 = 10$
TL214	0.021λ , 4.2Ω	$W1 = 22.35$, $W2 = 1.52$, $W3 = 22.35$, $W4$	$W1 = 880$, $W2 = 880$, $W3 = 880$, $W4 = 60$
TL215	0.049λ , 20.5Ω	$W1 = 3.81$, $W2 = 3.81$, $W3 = 3.81$	$W1 = 150$, $W2 = 150$, $W3 = 150$
TL217	0.016λ , 20.5Ω	$W = 3.81$, $L = 1.27$	$W = 150$, $L = 150$
TL218	0.034λ , 46.18Ω	$W = 1.27$, $L = 2.74$	$W = 50$, $L = 50$
TL219	0.036λ , 34.02Ω	$W = 1.98$, $L = 2.84$	$W = 78$, $L = 78$

(table cont. next page)

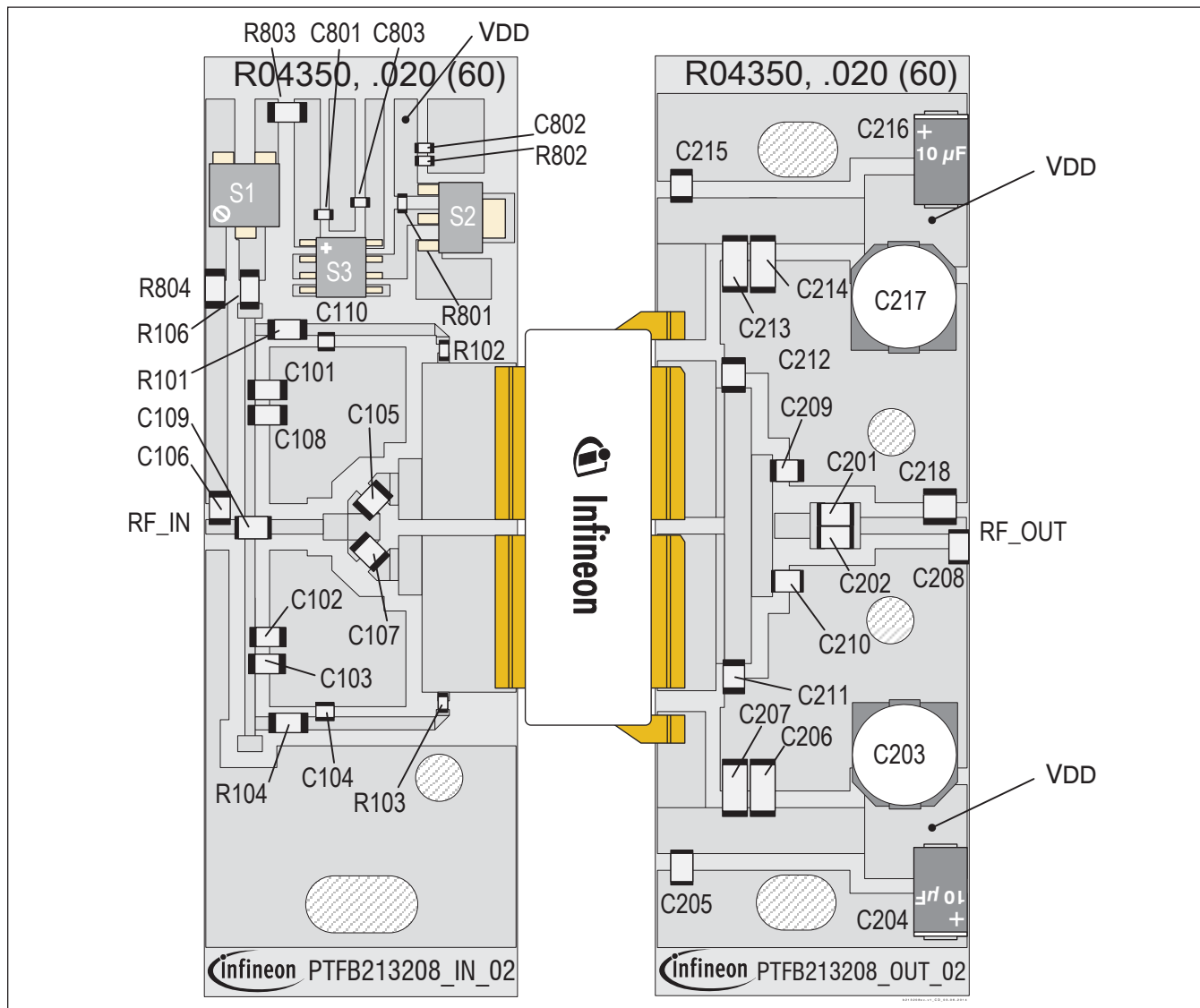
Reference Circuit (cont.)

Electrical Characteristics at 2170 MHz (output cont.)

Transmission Line	Electrical Characteristics	Dimensions: mm	Dimensions: mils
TL223, TL224	0.018λ , 100.15Ω	$W1 = 0.25$, $W2 = 0.25$, $W3 = 1.52$	$W1 = 10$, $W2 = 10$, $W3 = 60$
TL229, TL232	0.009λ , 8.46Ω	$W = 10.54$, $L = 0.65$	$W = 415$, $L = 415$
TL230, TL234	0.064λ , 7.13Ω	$W = 12.7$, $L = 4.8$	$W = 500$, $L = 500$
TL235	0.016λ , 20.5Ω	$W = 3.81$, $L = 1.27$	$W = 150$, $L = 150$
TL236, TL243	0.012λ , 11.33Ω	$W = 7.62$, $L = 0.94$	$W = 300$, $L = 300$
TL237, TL251, TL242	0.027λ , 11.33Ω	$W1 = 7.62$, $W2 = 7.62$, $W3 = 2.03$	$W1 = 300$, $W2 = 300$, $W3 = 80$
TL238, TL241, TL248	0.029λ , 20.5Ω	$W1 = 3.81$, $W2 = 3.81$, $W3 = 2.29$	$W1 = 150$, $W2 = 150$, $W3 = 90$
TL239	0.019λ , 46.18Ω	$W1 = 1.27$, $W2 = 1.27$, $W3 = 1.52$	$W1 = 50$, $W2 = 50$, $W3 = 60$
TL240	0.036λ , 46.18Ω	$W = 1.27$, $L = 2.97$	$W = 50$, $L = 50$
TL244	0.049λ , 20.5Ω	$W1 = 3.81$, $W2 = 3.81$, $W3 = 3.81$	$W1 = 150$, $W2 = 150$, $W3 = 150$
TL245	0.100λ , 20.5Ω	$W = 3.81$, $L = 7.8$	$W = 150$, $L = 150$
TL246	0.017λ , 20.5Ω	$W = 3.81$, $L = 1.3$	$W = 150$, $L = 150$
TL247	0.013λ , 11.33Ω	$W = 7.62$, $L = 1.02$	$W = 300$, $L = 300$
TL249	0.091λ , 20.5Ω	$W = 3.81$, $L = 7.11$	$W = 150$, $L = 150$
TL250	0.029λ , 11.33Ω	$W = 7.62$, $L = 2.18$	$W = 300$, $L = 300$
TL252	0.019λ , 46.18Ω	$W1 = 1.27$, $W2 = 1.27$, $W3 = 1.52$	$W1 = 50$, $W2 = 50$, $W3 = 60$, $= 0$

See next page for assembly information

Reference Circuit (cont.)



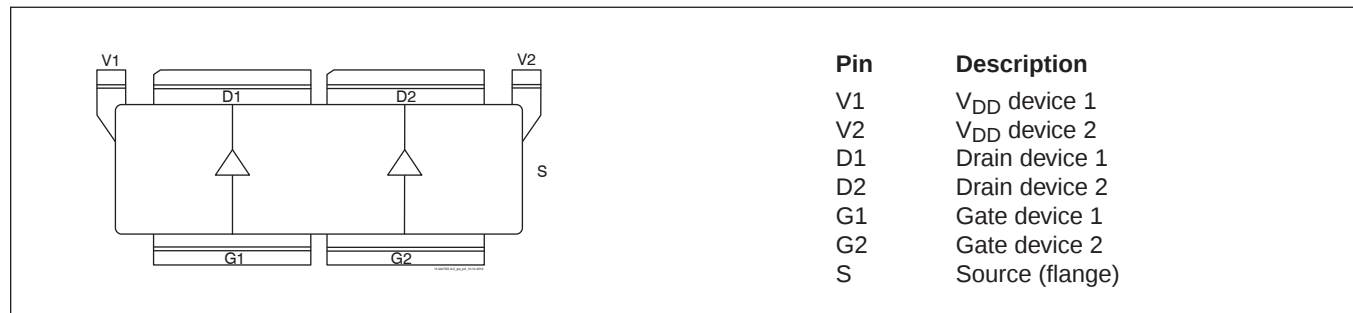
Reference circuit assembly diagram (not to scale)

Reference Circuit (cont.)

Components Information

Component	Description	Manufacturer	P/N
Input			
C101, C103	Chip capacitor, 1 μ F	Panasonic Electronic Components	ECJ-3VB1H104K
C102, C108	Chip capacitor, 4.7 μ F	Panasonic Electronic Components	ECS-T1CY475R
C104, C110	Chip capacitor, 10 pF	ATC	ATC100A100JW150XB
C105, C107, C109	Chip capacitor, 10 pF	ATC	ATC100B100JW500XB
C106	Chip capacitor, 1.50 pF	ATC	ATC100B1R5CW500XB
C801, C802, C803	Chip capacitor, 1,000 pF	Panasonic Electronic Components	ECJ-1VB1H102
R101	Resistor, 10 Ω	Panasonic Electronic Components	ERJ-8GEYJ100V
R102, R103	Resistor, 0.00 Ω	Panasonic Electronic Components	ERJ-3GEY0R00V
R104, R106, R804	Resistor, 10 Ω	Panasonic Electronic Components	ERJ-8GEYJ100V
R801	Resistor, 1,200 Ω	Panasonic Electronic Components	ERJ-3GEYJ122V
R802	Resistor, 1,300 Ω	Panasonic Electronic Components	ERJ-3GEYJ132V
R803	Resistor, 100 Ω	Panasonic Electronic Components	ERJ-8GEYJ101V
S1	Potentiometer, 2k Ω	Bourns Inc	3224W-1-202E
S2	Transistor	Infineon Technologies	BCP56
S3	Voltage Regulator	Texas Instruments	LM7805
Output			
C201, C202	Chip capacitor, 10 pF	ATC	ATC100B100JW500XB
C203, C217	Capacitor, 100 μ F	Panasonic Electronic Components	EEE-FP1V101AP
C204, C216	Capacitor, 10 μ F	AVX Corporation	TPSE106K050R0400
C205, C215	Capacitor, 10 μ F	Taiyo Yuden	UMK325C7106MM-T
C206, C214	Chip capacitor, 1 μ F	TDK Corporation	C4532X7R2A105M230KA
C207, C213	Chip capacitor, 2.2 μ F	TDK Corporation	C4532X7R1H225M160KA
C208	Chip capacitor, 0.20 pF	ATC	ATC100B0R2BW500XB
C209, C210	Chip capacitor, 0.30 pF	ATC	ATC100B0R3CW500XB
C211, C212	Chip capacitor, 1.30 pF	ATC	ATC100B1R3CW500XB
C218	Chip capacitor, 1.50 pF	ATC	ATC100B1R5CW500XB

Pinout Diagram (top view)



Lead connections for PTFB213208SV

Package Outline Specifications

Package H-37275G-6/2 (formed leads)

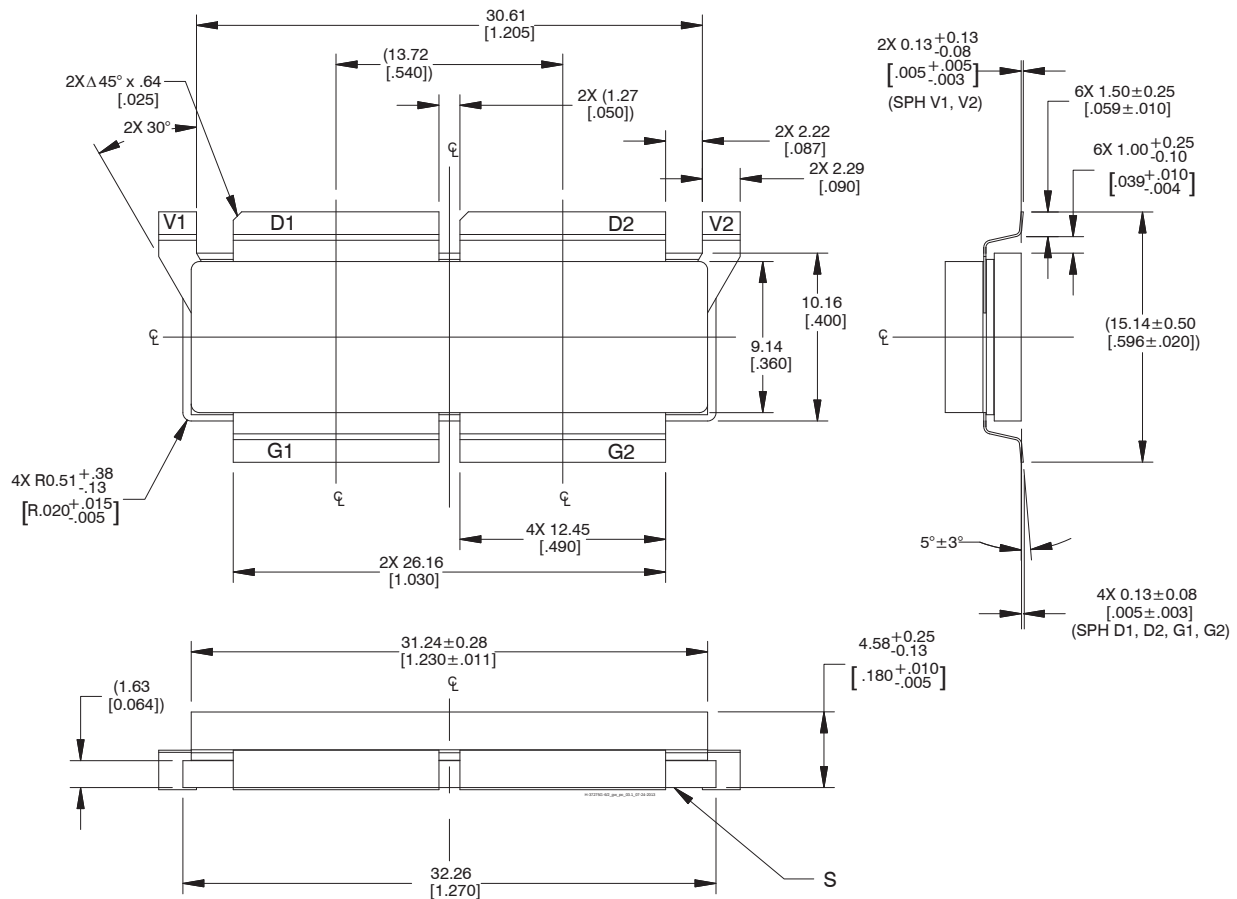


Diagram Notes—unless otherwise specified:

1. Interpret dimensions and tolerances per ASME Y14.5M-1994.
2. Primary dimensions are mm. Alternate dimensions are inches.
3. All tolerances ± 0.127 [.005].
4. Pins: D1, D2 – drain, G1, G2 – gate, S – source, V1, V2 – V_{DD}.
5. Lead thickness: 0.13 + 0.051/–0.025 [.005 + .002/–.001].
6. Gold plating thickness: 1.14 ± 0.38 micron [45 ± 15 microinch].

Find the latest and most complete information about products and packaging at the Infineon Internet page (<http://www.infineon.com/rfpower>)

Revision History

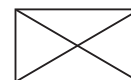
Revision	Date	Data Sheet	Page	Subjects (major changes compared to previous revision)
01	2012-02-07	Advance	All	Data Sheet reflects advance specification for product development
02	2013-05-17	Production	All	Data Sheet reflects released product specification Product released: Specifications updated; circuit and other information added
03	2014-03-06	Production	All 1 2 4 7 (10), 11 12	New package changes product to Version 2. Clarify graph and table labels. Specify output power for thermal resistance specification, update ordering table & pinout diagram. Misc. corrections and relabeling of three graphs. Er corrected to 3.66. Add manufacturer name to components table. New package: diagram and information.
04	2014-08-20	Production	12	Correct lead measurements in diagram and notes

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Any information within this document that you feel is wrong, unclear or missing at all?
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